

P-Channel 60 V (D-S) MOSFET

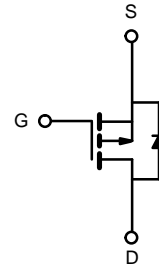
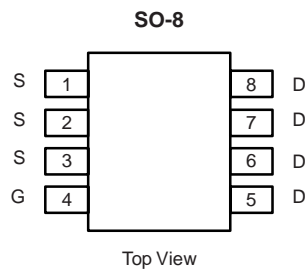
PRODUCT SUMMARY	
V_{DS} (V)	-60
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.050
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.060
I_D (A) per leg	-8

FEATURES

- TrenchFET® power MOSFET
- 100 % R_g and UIS tested



RoHS
COMPLIANT
HALOGEN
FREE



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25$ °C	-8
		$T_C = 125$ °C	-4.75
Continuous Source Current (Diode Conduction)	I_S	-4.5	A
Pulsed Drain Current ^a	I_{DM}	-32	
Single Pulse Avalanche Current	I_{AS}	-22.4	
Single Pulse Avalanche Energy	E_{AS}	25	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	
		$T_C = 125$ °C	1.67
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	110	°C/W
Junction-to-Foot (Drain)	R_{thJF}	30	

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.

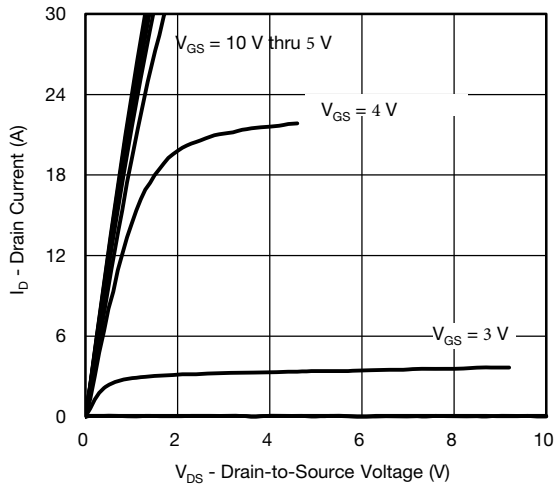
SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	-60	-	-	V	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	-1.0		-2.5		
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = -60\text{ V}$	-	-	-1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = -60\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	-50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = -60\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$	-	-	-150	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = -10\text{ V}$	$V_{DS} \leq -5\text{ V}$	-30	-	A	
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -4.3\text{ A}$	-	0.050	-	Ω
		$V_{GS} = -10\text{ V}$	$I_D = -4.3\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$	-	0.070	-	
		$V_{GS} = -10\text{ V}$	$I_D = -4.3\text{ A}$, $T_J = 175\text{ }^\circ\text{C}$	-	0.080	-	
		$V_{GS} = -4.5\text{ V}$	$I_D = -3.8\text{ A}$	-	0.060	-	
Forward Transconductance ^b	g_{fs}	$V_{DS} = -15\text{ V}$, $I_D = -4.3\text{ A}$		-	13	S	
Dynamic^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = -30\text{ V}$, $f = 1\text{ MHz}$	-	1530	1910	μF
Output Capacitance	C_{oss}			-	334	417	
Reverse Transfer Capacitance	C_{rss}			-	114	142	
Total Gate Charge ^c	Q_g	$V_{GS} = -10\text{ V}$	$V_{DS} = -30\text{ V}$, $I_D = -5\text{ A}$	-	43.4	65	nC
Gate-Source Charge ^c	Q_{gs}			-	4.7	-	
Gate-Drain Charge ^c	Q_{gd}			-	9	-	
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.3	2.5	4	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -30\text{ V}$, $R_L = 8.8\text{ }\Omega$ $I_D \cong -5\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 1\text{ }\Omega$		-	11	17	ns
Rise Time ^c	t_r			-	11	17	
Turn-Off Delay Time ^c	$t_{d(off)}$			-	35	52	
Fall Time ^c	t_f			-	6	9	
Source-Drain Diode Ratings and Characteristics^b							
Pulsed Current ^a	I_{SM}			-	-	-32	A
Forward Voltage	V_{SD}	$I_F = -2.8\text{ A}$, $V_{GS} = 0\text{ V}$		-	-0.8	-1.2	V

Notes

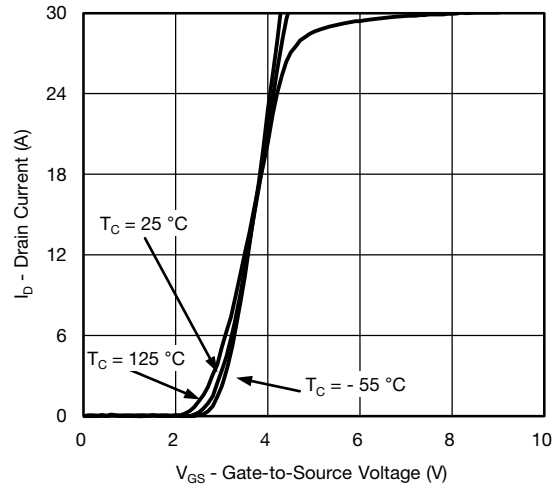
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

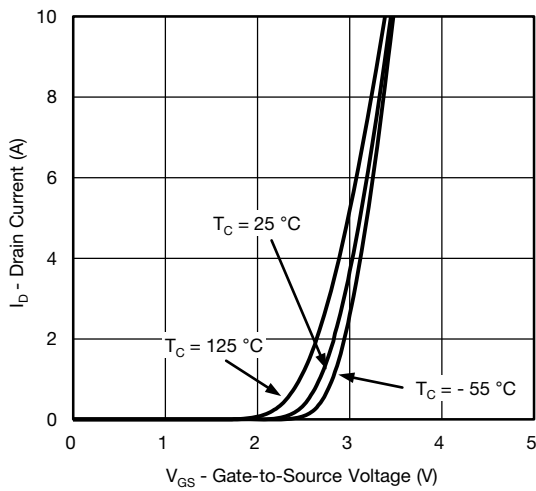
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



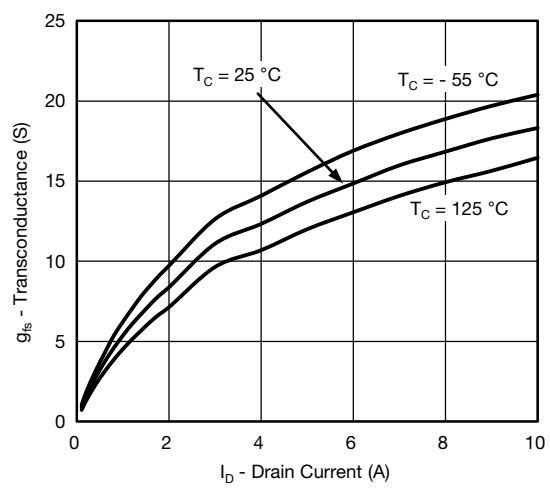
Output Characteristics



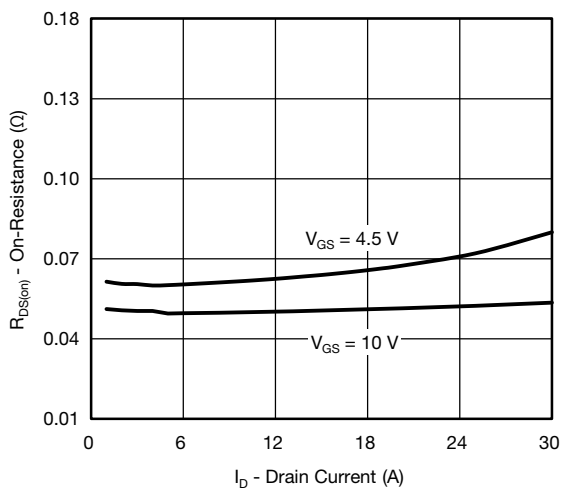
Transfer Characteristics



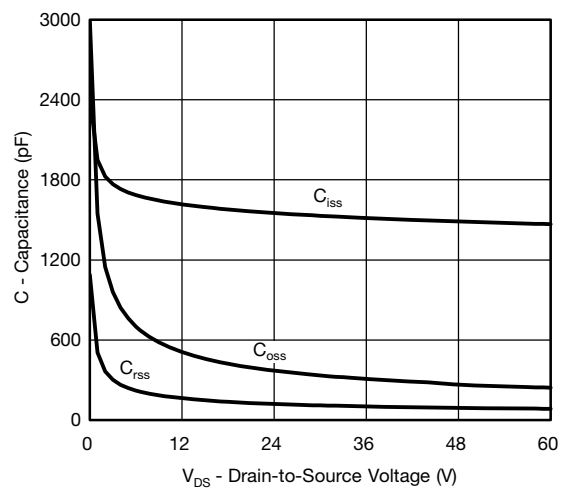
Transfer Characteristics



Transconductance



On-Resistance vs. Drain Current

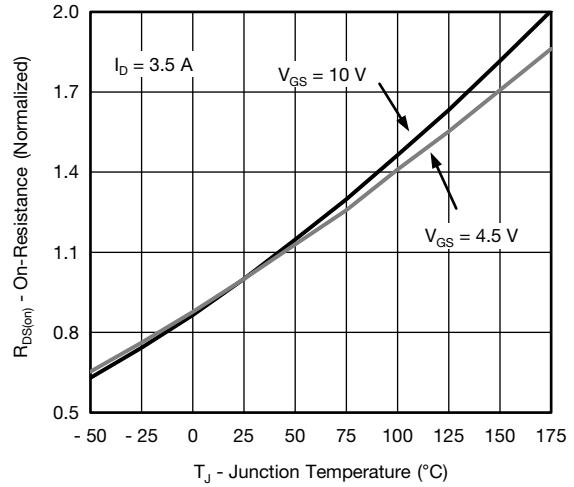


Capacitance

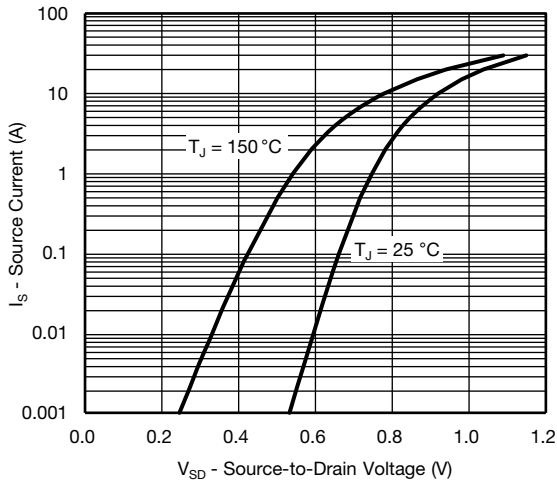
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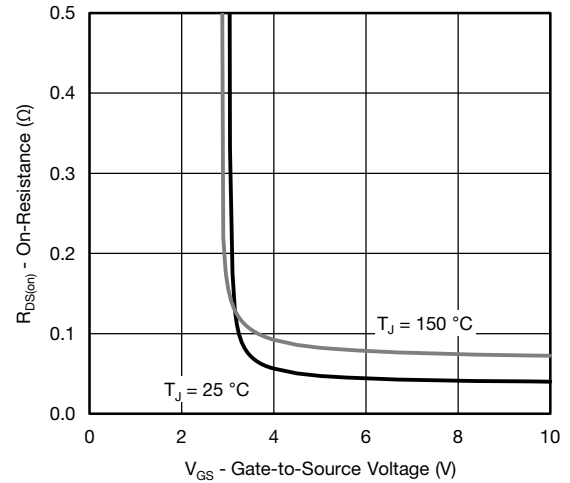
Gate Charge



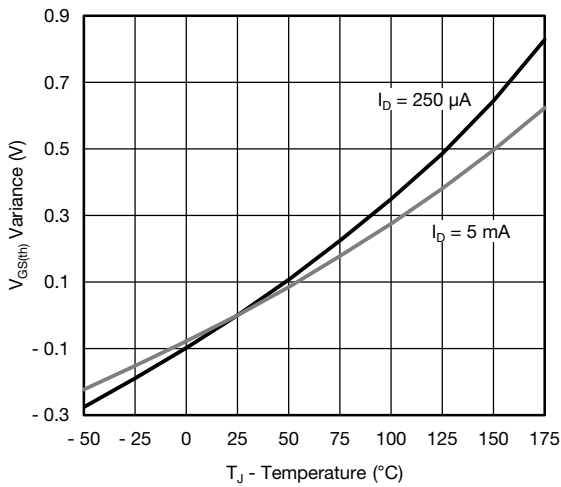
On-Resistance vs. Junction Temperature



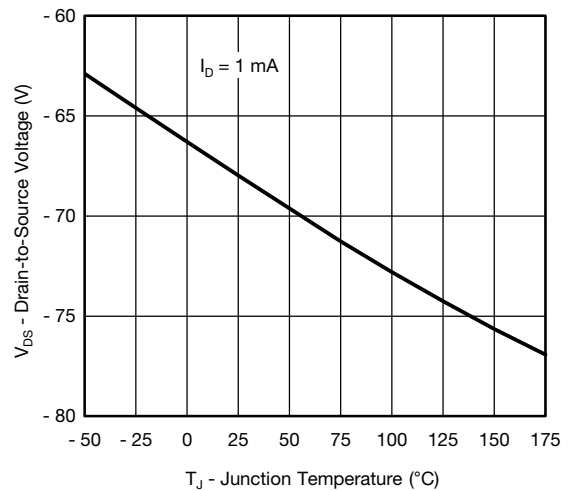
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

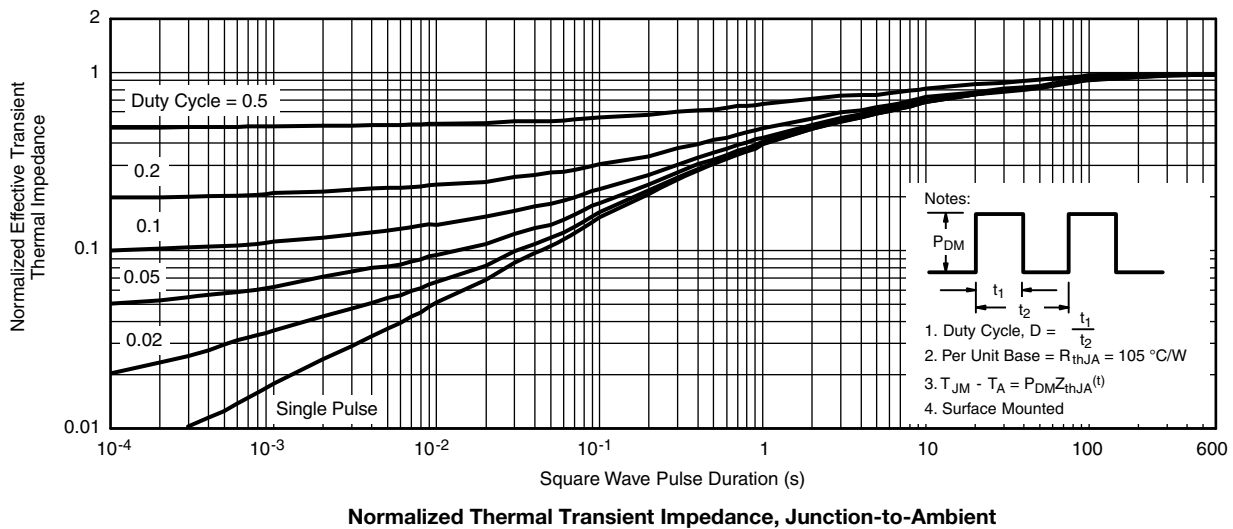
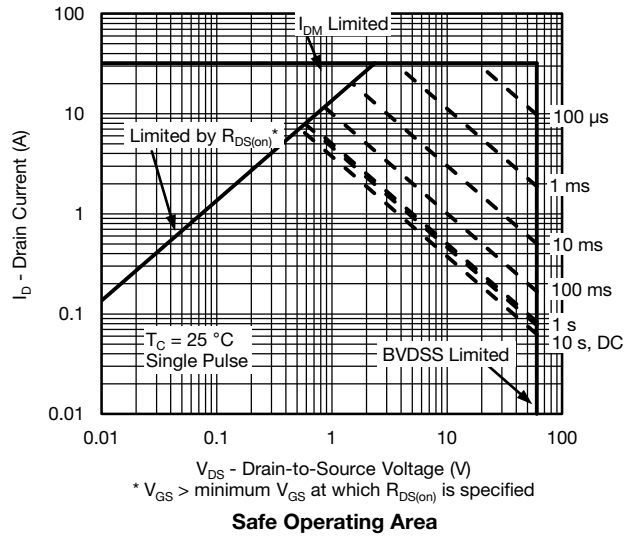


Threshold Voltage

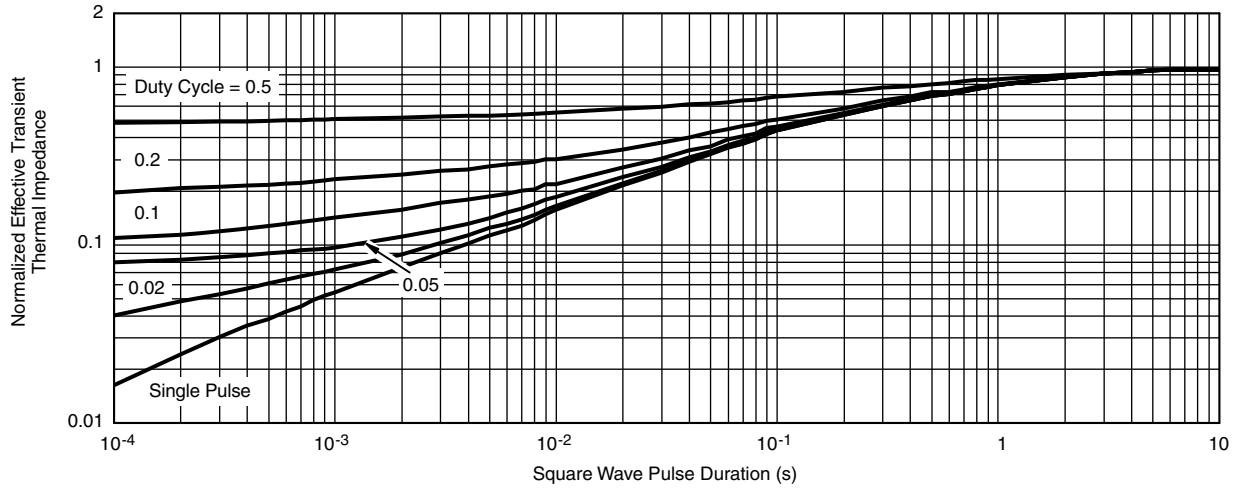


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

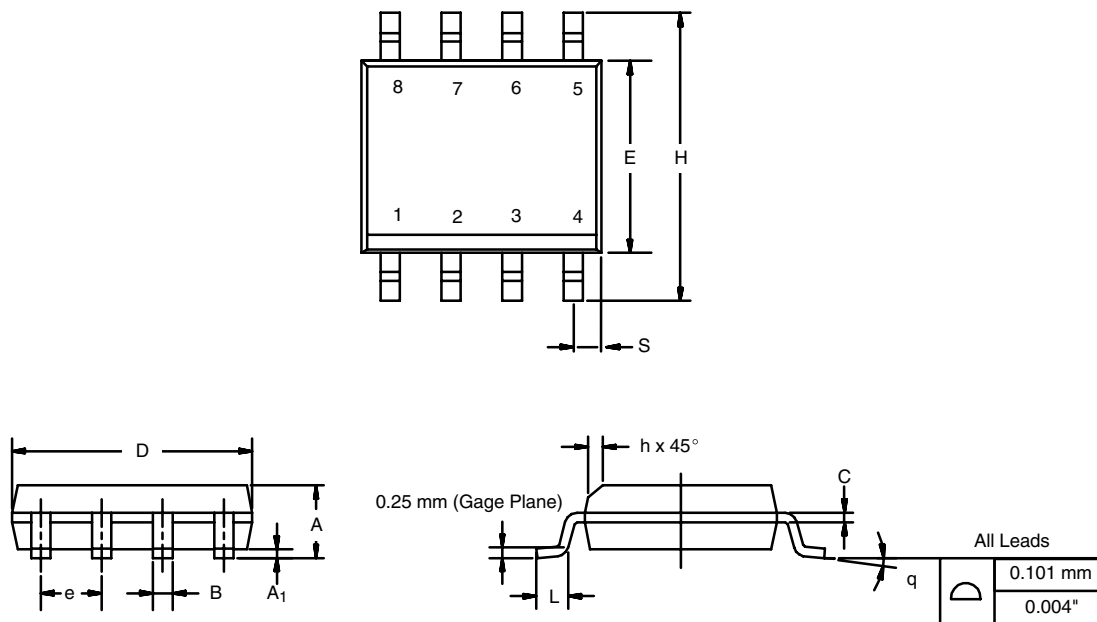


Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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